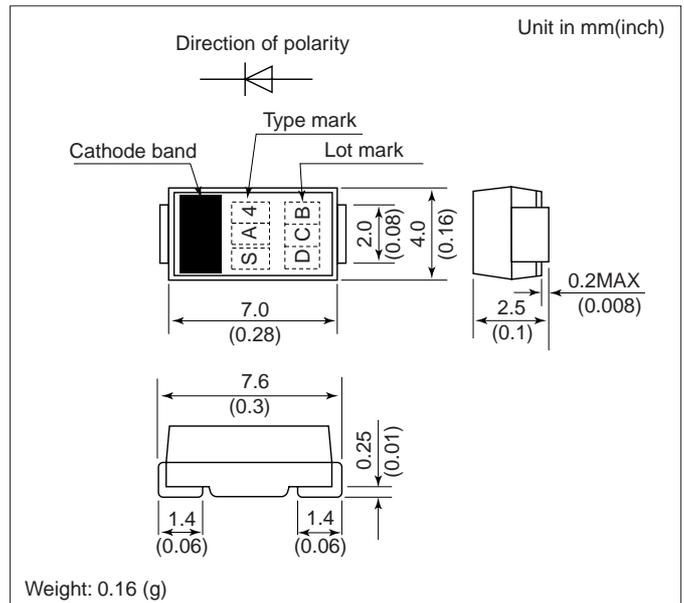


DSM3MA

FEATURES

- For general purpose
- High heat-resistant due to glass passivation.

OUTLINE DRAWING



ABSOLUTE MAXIMUM RATINGS

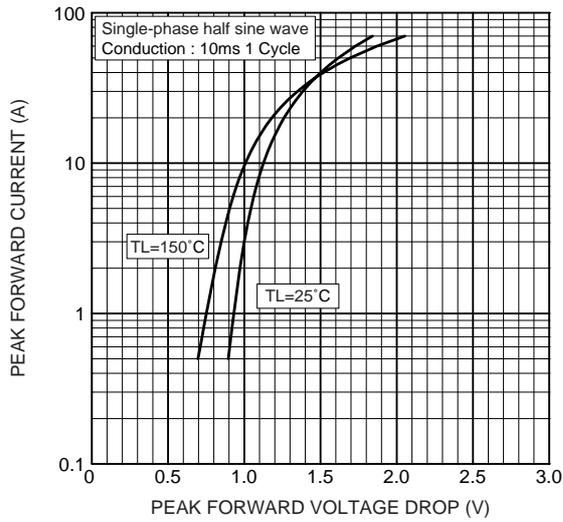
Items	Type		DSM3MA1	DSM3MA2	DSM3MA4
Repetitive Peak Reverse Voltage	V_{RRM}	V	100	200	400
Average Forward Current	$I_{F(AV)}$	A	3.0 (Single-phase half sine wave 180° conduction TL = 108°C)		
Surge(Non-Repetitive) Forward Current	I_{FSM}	A	80 (Without PIV, 10ms conduction, Tj = 40°C start)		
I ² t Limit Value	I ² t	A ² s	25.6 (Time = 2 ~ 10ms, I = RMS value)		
Operating Junction Temperature	T _j	°C	-40 ~ +150		
Storage Temperature	T _{stg}	°C	-40 ~ +150		

CHARACTERISTICS(T_L=25°C)

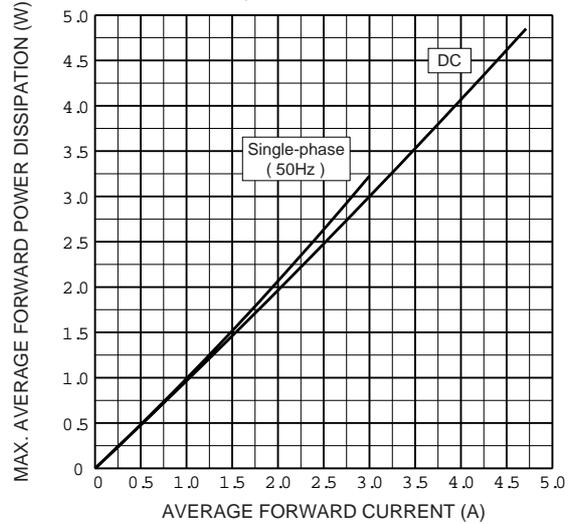
Items	Symbols	Units	Min.	Typ.	Max.	Test Conditions
Peak Reverse Current	I_{RRM}	μA	-	-	20	Rated V_{RRM}
					10	
Peak Forward Voltage	V_{FM}	V	-	-	1.0	$I_{FM}=3.0A_p$, Single-phase half sine wave 1 cycle
Steady State Thermal Impedance	$R_{th(j-a)}$	°C/W	-	-	80	On glass-epoxi substrate (□ 50mm) Soldering land (□ 10mm)
	$R_{th(j-l)}$				13	

DSM3MA

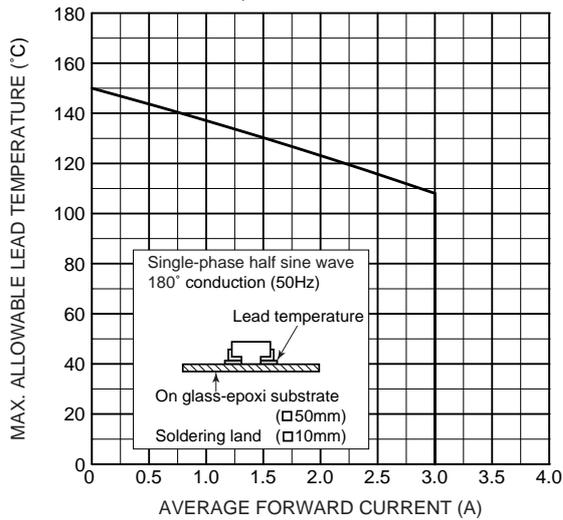
Forward characteristics



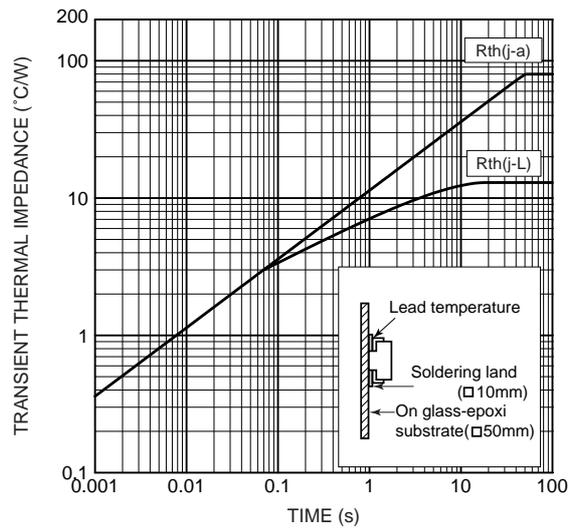
Max. average forward power dissipation (Resistive or inductive load)



Max. allowable lead temperature (Resistive or inductive load)



Transient thermal impedance



HITACHI POWER SEMICONDUCTORS

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